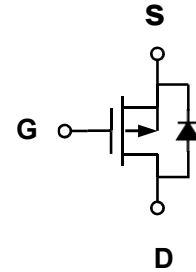




P-Channel Enhancement Mode Power MOSFET

Description

The MX3407 uses advanced trench technology to provide excellent $R_{DS(ON)}$. This device is suitable for use as a load switch or in PWM applications.



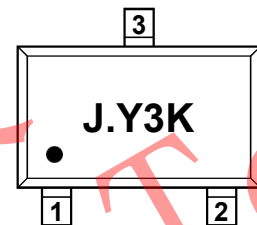
Schematic diagram

General Features

- ◆ $V_{DS} = -30V$, $I_D = -4.3A$
- ◆ $R_{DS(ON)}(Typ.) < 100m\Omega @ V_{GS} = -4.5V$
- ◆ $R_{DS(ON)}(Typ.) < 50m\Omega @ V_{GS} = -10V$
- ◆ High power and current handling capability
- ◆ Lead free product is acquired
- ◆ Surface mount package

Application

- ◆ PWM applications
- ◆ Load switch
- ◆ Power management



Marking and pin assignment



Sot-23-3 top view

Ordering Information

Part Number	Marking	Storage Temperature	Package	Devices Per Reel
MX3407	J.Y3K	-55°C to +150°C	SOT-23-3	3000

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

parameter	symbol	limit	unit
Drain-source voltage	V_{DS}	-30	V
Gate-source voltage	V_{GS}	±20	V
Drain current-continuous Drain Current-Pulsed (Note 1)	I_D	-4.3	A
	I_{DM}	-20	A
Drain-source Diode forward current	I_S	-1.25	A
Maximum power dissipation	P_D	1.5	W
Operating junction Temperature range	T_j	-55—150	°C



Electrical Characteristics (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
OFF Characteristics						
Drain-source breakdown voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-30	-	-	V
Zero gate voltage drain current	I_{DSS}	$V_{DS}=-24V, V_{GS}=0V$	-	-	-1	μA
Gate-body leakage	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 20V$	-	-	± 100	nA
ON Characteristics						
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1.4	-1.6	-2.4	V
Drain-source on-state resistance	$R_{DS(ON)}$	$V_{GS}=-10V, I_D=-4.3A$	-	38	50	m Ω
		$V_{GS}=-4.5V, I_D=-4A$	-	60	100	m Ω
Forward transconductance	g_{fs}	$V_{GS}=-5V, I_D=-4.1A$	5.5	-	-	S
Dynamic Characteristics						
Input capacitance	C_{ISS}	$V_{DS}=-15V, V_{GS}=0V$ $f=1.0MHz$	-	700	-	pF
Output capacitance	C_{OSS}		-	120	-	
Reverse transfer capacitance	C_{RSS}		-	75	-	
Switching Characteristics						
Turn-on delay time	$t_{D(ON)}$	$V_{DD}=-15V$ $RL=3.6\Omega$	-	9	-	ns
Rise time	t_r		-	5	-	
Turn-off delay time	$t_{D(OFF)}$	$V_{GS}=-10V$ $R_{GEN}=3\Omega$	-	28	-	
Fall time	t_f		-	13.5	-	
Total gate charge	Q_g	$V_{DS}=-15V, I_D=-4.2A$ $V_{GS}=-4.5V$	-	14	-	nC
Gate-source charge	Q_{gs}		-	3.1	-	
Gate-drain charge	Q_{gd}		-	3.	-	
DRAIN-SOURCE DIODE CHARACTERISTICS						
Diode forward voltage	V_{SD}	$V_{GS}=0V, I_S=-4.2A$	-	-	-1.2	V

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to product



Typical Performance Characteristics

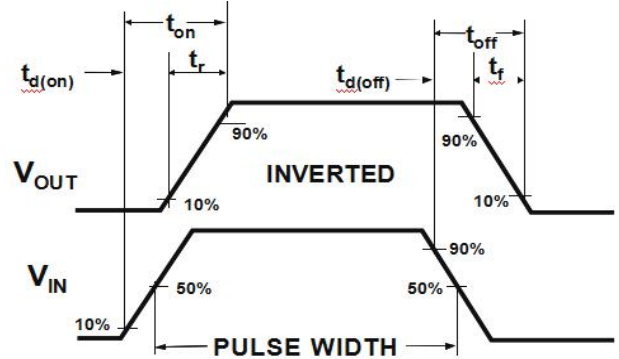
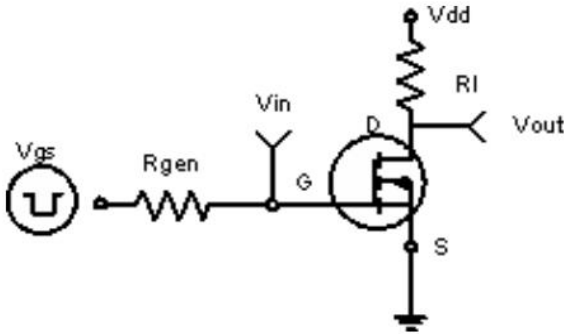


Figure 1: Switching Test Circuit

Figure 2: Switching Waveforms

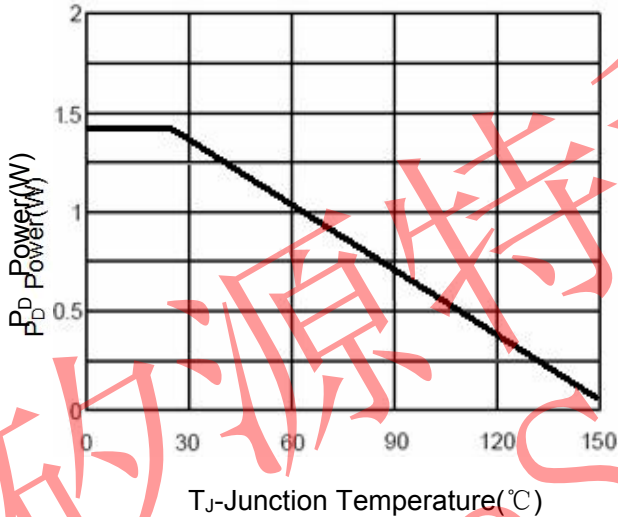


Figure 3 Power Dissipation

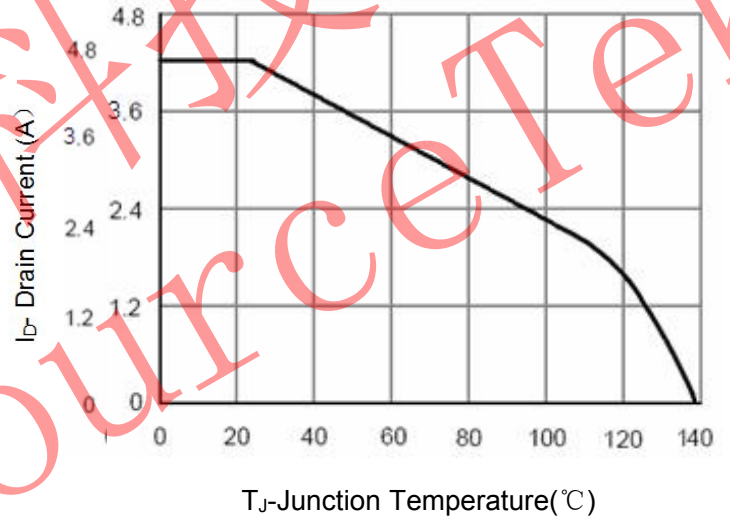


Figure 4 Drain Current

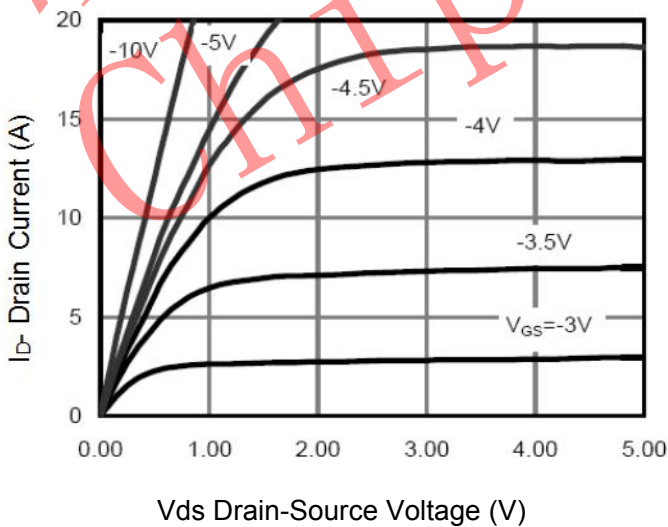


Figure 5 Output CHARACTERISTICS

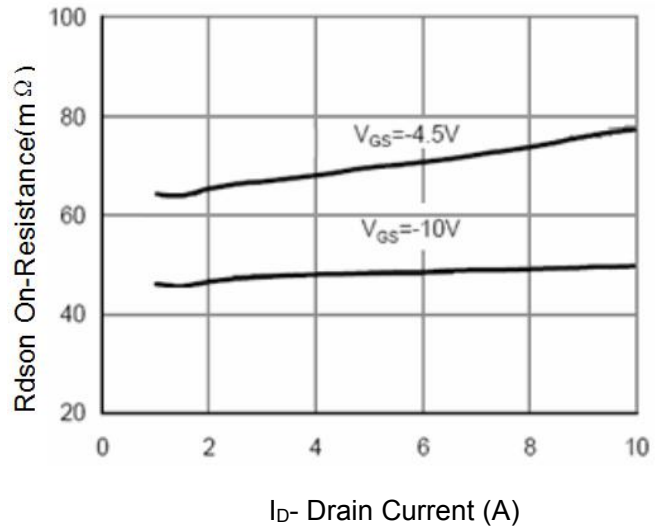


Figure 6 Drain-Source On-Resistance

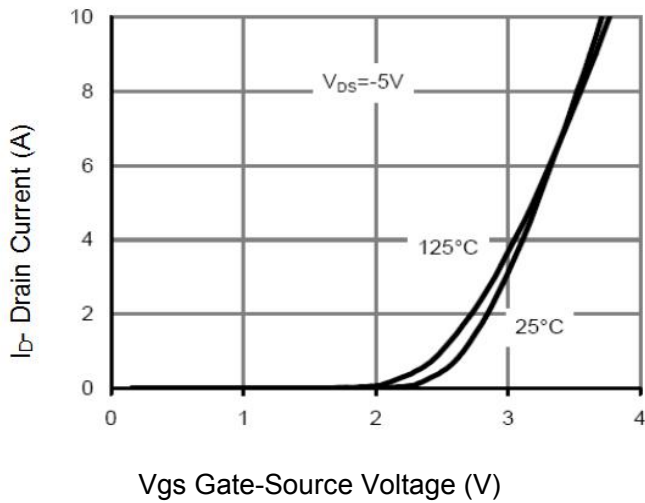


Figure 7 Transfer Characteristics

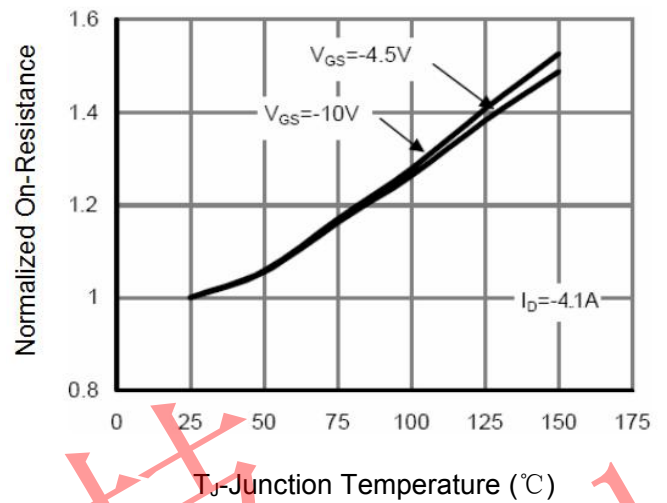


Figure 8 Drain-Source On-Resistance

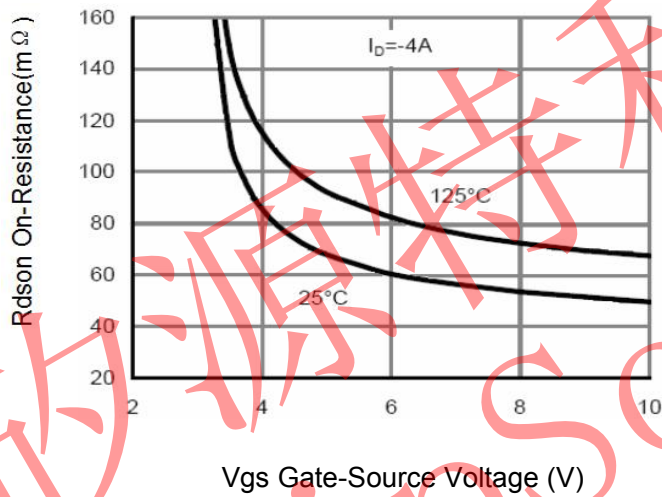


Figure 9 Rdson vs Vgs

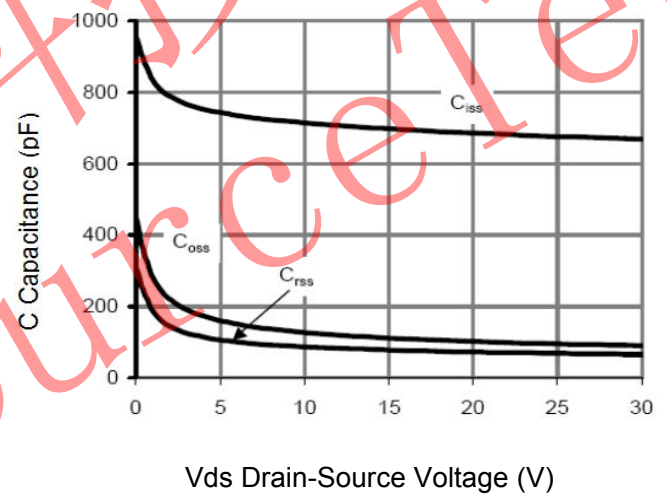


Figure 10 Capacitance vs Vds

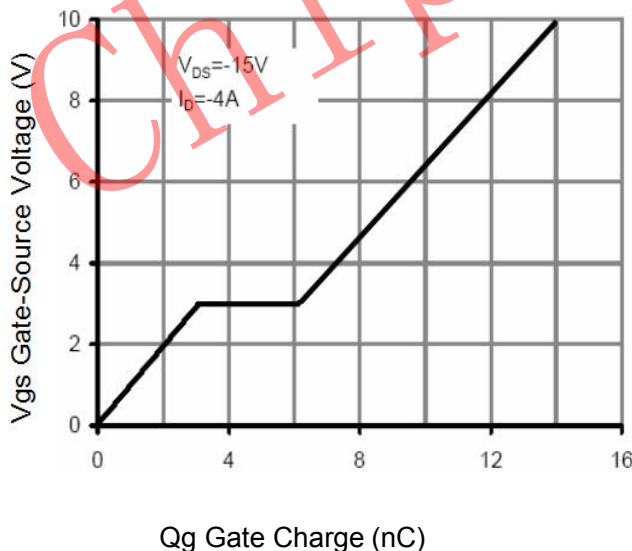


Figure 11 Gate Charge

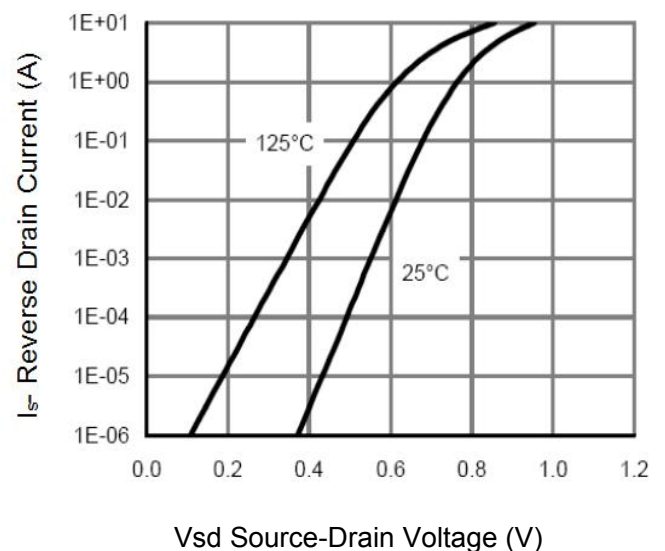


Figure 12 Source- Drain Diode Forward

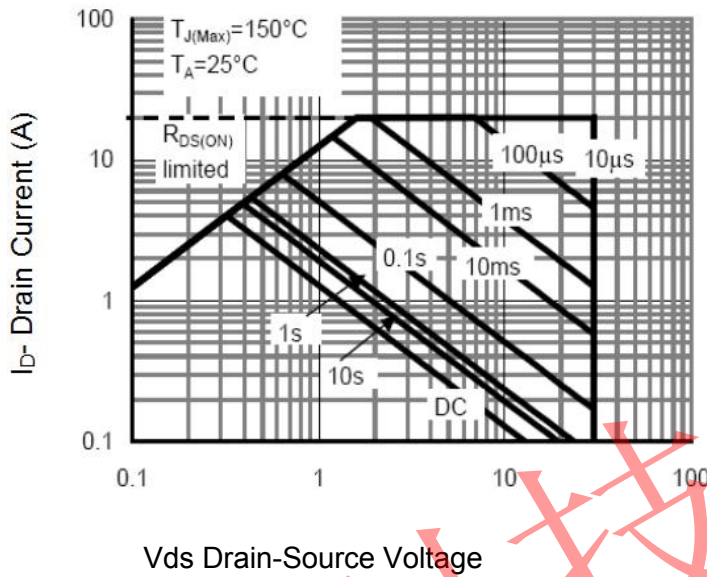


Figure 13 Safe Operation Area

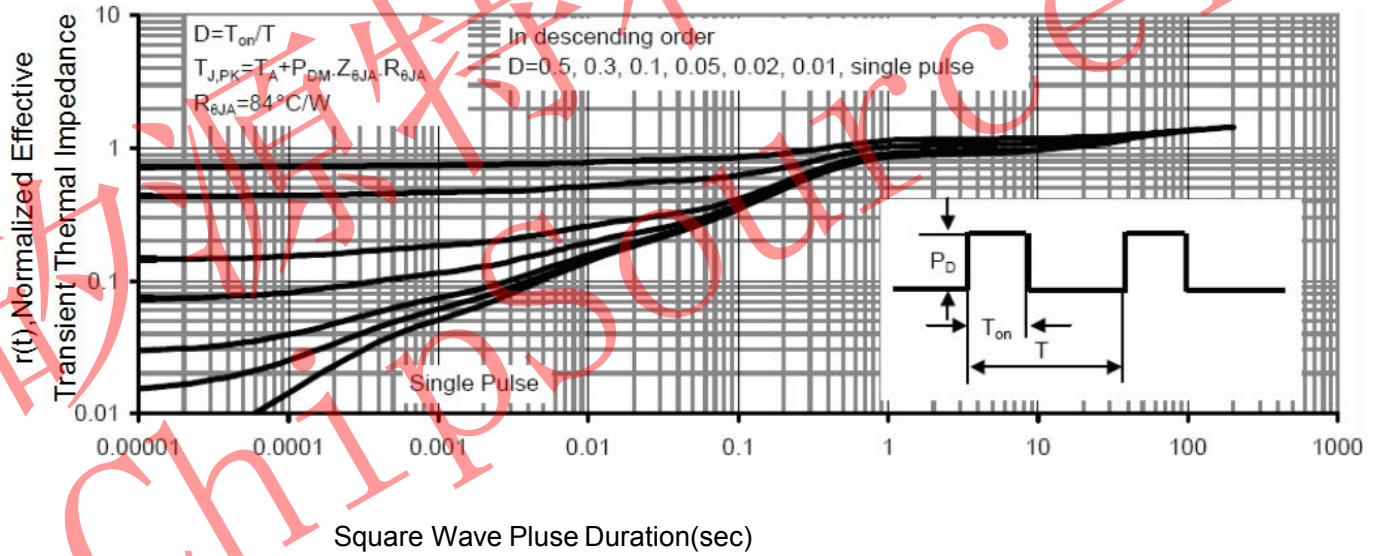
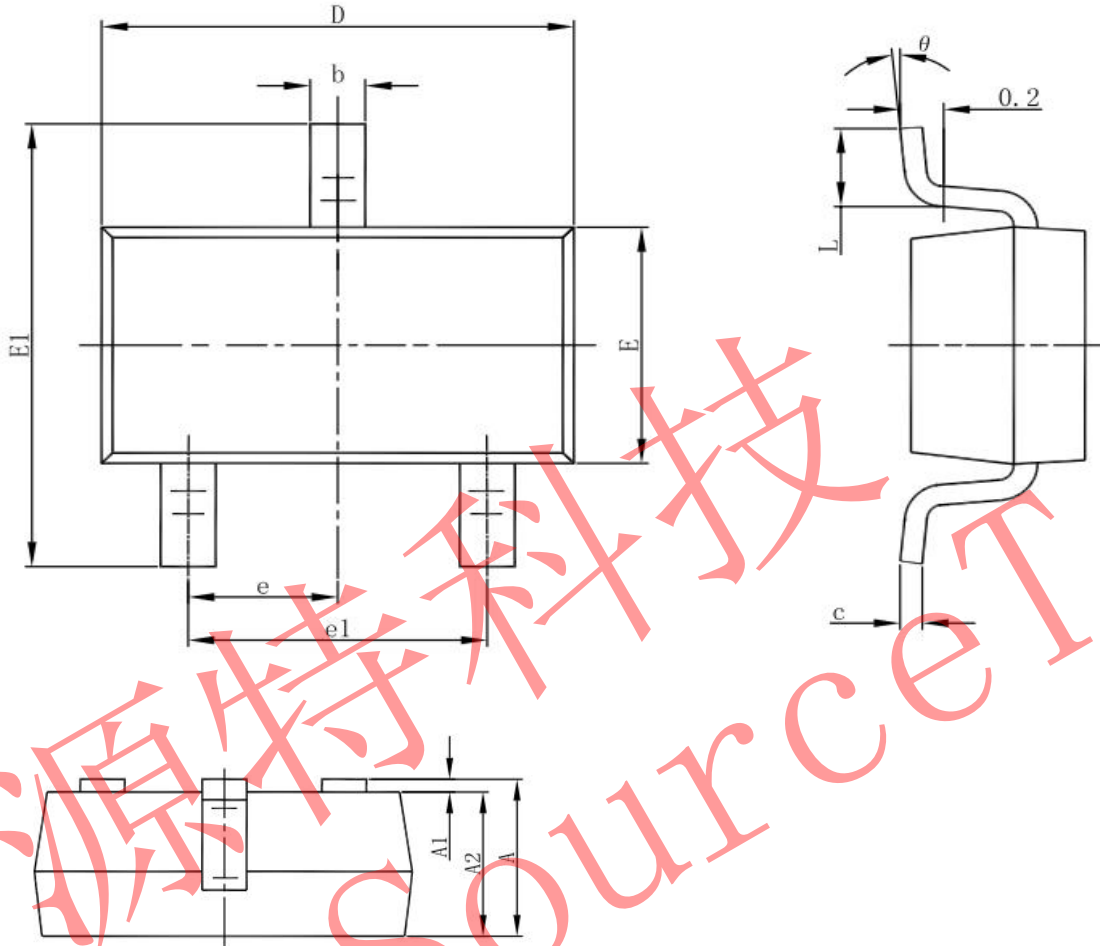


Figure 14 Normalized Maximum Transient Thermal Impedan



SOT-23 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°